N-Channel Silicon MOSFET

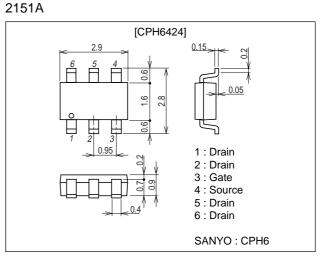


## Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

# **Package Dimensions**

unit : mm



# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱D		3	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	12	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm <sup>2</sup> X0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

## Electrical Characteristics at Ta=25°C

Symbol	Conditions	Ratings			Unit
		min	typ	max	Unit
V(BR)DSS	ID=1mA, VGS=0	60			V
IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0			1	μΑ
IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A	2.3	3.4		S
R <sub>DS</sub> (on)1	ID=1.5A, VGS=10V		110	145	mΩ
R <sub>DS</sub> (on)2	ID=1.5A, VGS=4V		150	215	mΩ
	V(BR)DSS IDSS IGSS VGS(off)  yfs  RDS(on)1	V(BR)DSS ID=1mA, VGS=0   IDSS VDS=60V, VGS=0   IGSS VGS=16V, VDS=0   VGS(off) VDS=10V, ID=1mA    yfs  VDS=10V, ID=1.5A   RDS(on)1 ID=1.5A, VGS=10V	V(BR)DSS ID=1mA, VGS=0 60   IDSS VDS=60V, VGS=0 60   IGSS VGS=±16V, VDS=0 1.2   VGS(off) VDS=10V, ID=1mA 1.2    yfs  VDS=10V, ID=1.5A 2.3   RDS(on)1 ID=1.5A, VGS=10V 1.2	Symbol Conditions min typ   V(BR)DSS ID=1mA, VGS=0 60 60   IDSS VDS=60V, VGS=0 60 60   IGSS VGS=416V, VDS=0 60 60   VGS(off) VDS=10V, ID=1mA 1.2 1.2   Iyfs VDS=10V, ID=1.5A 2.3 3.4   RDS(on)1 ID=1.5A, VGS=10V 110 110	Symbol Conditions min typ max   V(BR)DSS ID=1mA, VGS=0 60 1   IDSS VDS=60V, VGS=0 1 1   IGSS VGS=±16V, VDS=0 1 ±10   VGS(off) VDS=10V, ID=1mA 1.2 2.6    yfs  VDS=10V, ID=1.5A 2.3 3.4   RDS(on)1 ID=1.5A, VGS=10V 110 145

Marking : ZA

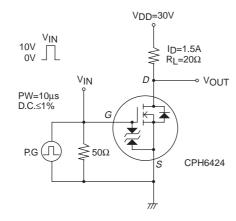
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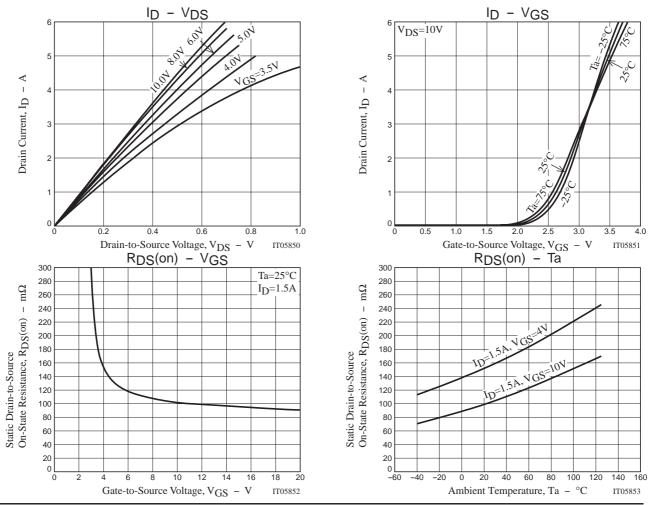
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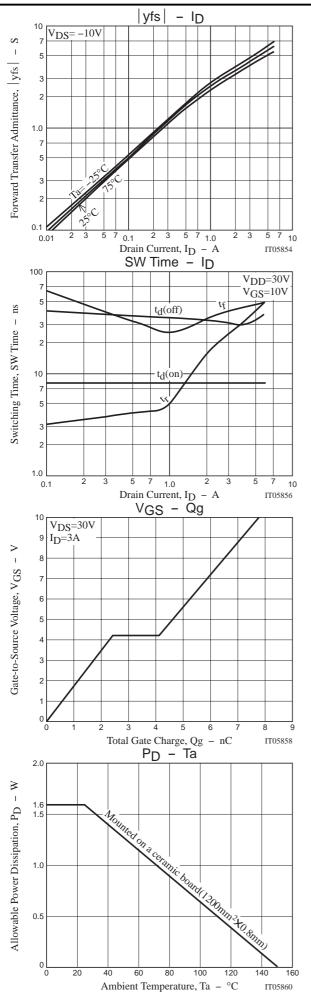
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

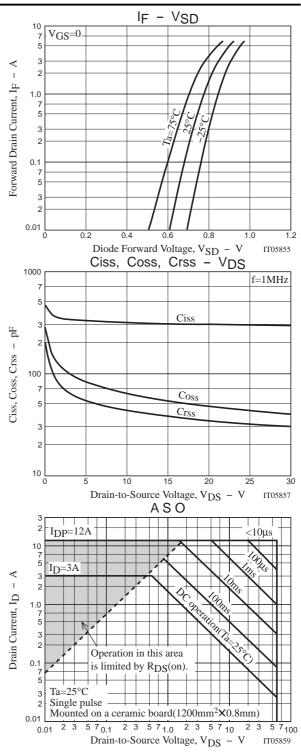
Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		266		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		54		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		34		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		8		ns
Rise Time	tr	See specified Test Circuit.		8		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		33		ns
Fall Time	tf	See specified Test Circuit.		30		ns
Total Gate Charge	Qg	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		7.8		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		2.4		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		1.7		nC
Diode Forward Voltage	VSD	IS=3A, VGS=0		0.84	1.2	V

### **Switching Time Test Circuit**









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